

LL914PF THRU LL4454PF

Silicon Epitaxial Planar Switching Diode

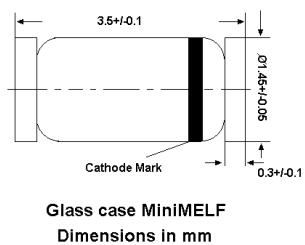
Features

- Lead Free
- Automatic surface mounting

Applications

- For general purpose and switching.

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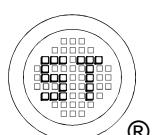
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	500	mW
Operation Junction Temperature	T_j	- 65 to + 175	°C
Storage Temperature Range	T_{stg}	- 65 to + 175	°C

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient Air ¹⁾	$R_{\theta JA}$	300	°C/W

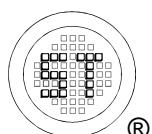
¹⁾ Valid provided that electrodes are kept at ambient temperature.



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Characteristics at $T_a = 25^\circ\text{C}$

Type	Peak Reverse Voltage	Aver. Rectified Current	Forward Voltage		Reverse Current		Reverse Recovery Time	
	V_{RM}	$I_{F(AV)}$	V_F	at I_F	I_R	at V_R	t_{rr}	Conditions
	(V)	Max.(mA)	Max.(V)	(mA)	Max.(nA)	(V)	Max.(ns)	
LL914PF	100	75	1	10	25	20	4	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}, R_L = 100 \Omega, \text{ to } I_R = 1 \text{ mA}$
LL4149PF	100	150	1	10	25	20	4	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}, R_L = 100 \Omega, \text{ to } I_R = 1 \text{ mA}$
LL4152PF	40	150	0.55	0.1	50	30	2	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}, R_L = 100 \Omega, \text{ to } I_R = 1 \text{ mA}$
LL4154PF	35	150	1	30	100	25	2	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}, R_L = 100 \Omega, \text{ to } I_R = 1 \text{ mA}$
LL4447PF	100	150	1	20	25	20	4	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}, R_L = 100 \Omega, \text{ to } I_R = 1 \text{ mA}$
LL4449PF	100	150	1	30	25	20	4	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}, R_L = 100 \Omega, \text{ to } I_R = 1 \text{ mA}$
LL4450PF	40	150	0.54	0.5	50	30	4	$I_F = I_R = 10 \text{ mA, to } I_R = 1 \text{ mA}$
LL4451PF	40	150	0.5	0.1	50	30	10	$I_F = I_R = 10 \text{ mA, to } I_R = 1 \text{ mA}$
LL4453PF	30	150	0.55	0.01	50	20	-	-
LL4454PF	75	150	1	10	100	50	4	$I_F = I_R = 10 \text{ mA, to } I_R = 1 \text{ mA}$



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Electrical Characteristics Curves

Fig 1. Forward Characteristics

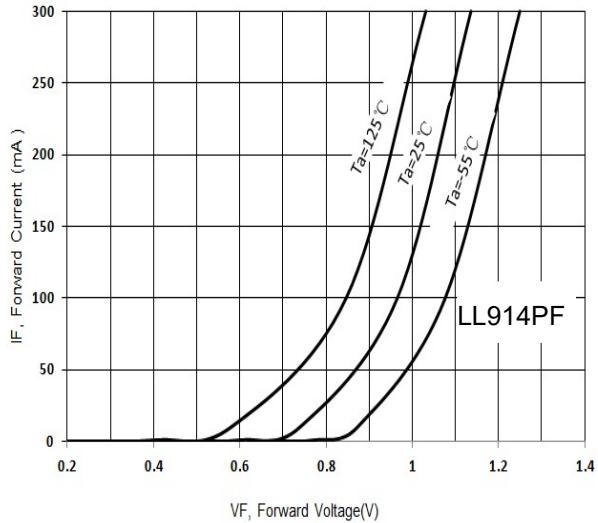


Fig 2. Reverse Characteristics

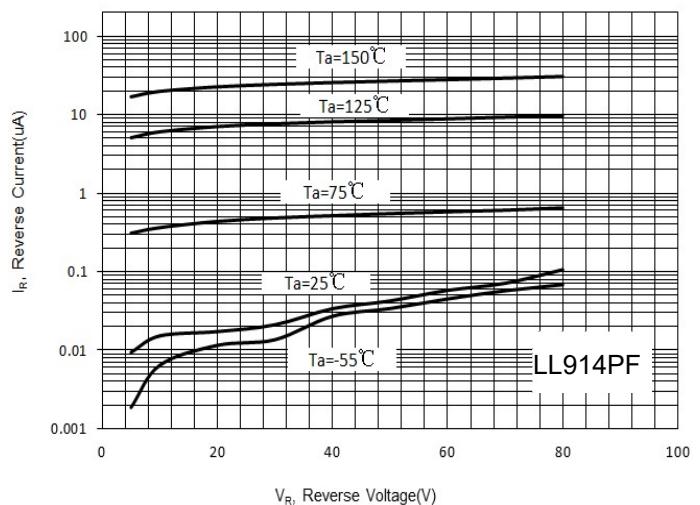


Fig 3. Junction Capacitance

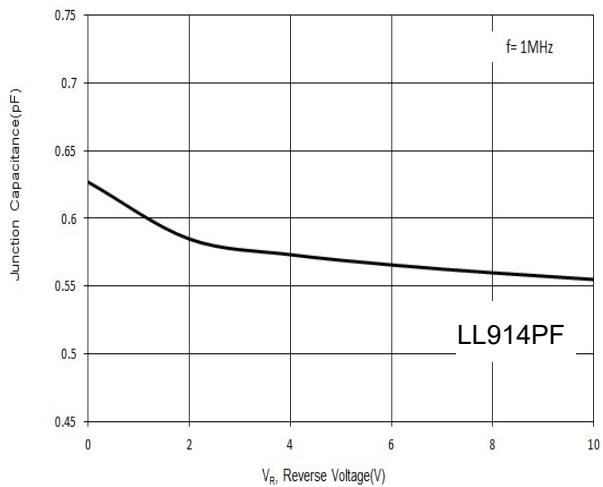


Fig 4. Power Derating Curves

